



10A, 45V - 150V Schottky Barrier Surface Mount Rectifier

FEATURES

- Low power loss, high efficiency
- Ideal for automated placement
- Guard ring for overvoltage protection
- High surge current capability
- Moisture sensitivity level: level 1, per J-STD-020
- RoHS Compliant
- Halogen-free according to IEC 61249-2-21

APPLICATIONS

- Switching mode power supply (SMPS)
- Adapters
- DC to DC converters

MECHANICAL DATA

- Case: TO-263AB (D²PAK)
- Molding compound meets UL 94V-0 flammability rating
- Terminal: Matte tin plated leads, solderable per J-STD-002
- Meet JESD 201 class 1A whisker test
- Polarity: As marked
- Weight: 1.37g (approximately)

KEY PARAMETERS			
PARAMETER	VALUE	UNIT	
l _F	10	Α	
V_{RRM}	45 - 150	V	
I _{FSM}	120	Α	
T_{JMAX}	150	°C	
Package	TO-263AB	(D ² PAK)	
Configuration	Dual d	ies	

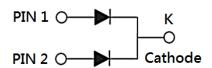








TO-263AB (D²PAK)



ABSOLUTE MAXIMUM RATINGS (T _A = 25°C unless otherwise noted)						
PARAMETER	SYMBOL	MBRS 1045 CT-Y	MBRS 1060 CT-Y	MBRS 10100 CT-Y	MBRS 10150 CT-Y	UNIT
Marking code on the device		MBRS 1045CT	MBRS 1060CT	MBRS 10100CT	MBRS 10150CT	
Repetitive peak reverse voltage	V_{RRM}	45	60	100	150	V
Reverse voltage, total rms value	$V_{R(RMS)}$	31	42	70	105	V
Forward current	I _F	10			Α	
Surge peak forward current, 8.3ms single half sine wave superimposed on rated load	I _{FSM}	120			Α	
Peak repetitive reverse surge current ⁽¹⁾	I_{RRM}	1			Α	
Peak repetitive forward current (Rated V_R , Square wave, 20KHz)	I _{FRM}	10		А		
Critical rate of rise of off-state voltage	dv/dt	dt 10,000		V/µs		
Junction temperature	TJ	-55 to +150		°C		
Storage temperature	T _{STG}	-55 to +150		°C		

Notes:

1. $tp = 2.0\mu s$, 1.0KHz



THERMAL PERFORMANCE				
PARAMETER	SYMBOL	TYP	UNIT	
Junction-to-case thermal resistance	R _{eJC}	2	°C/W	

PARAMETER		CONDITIONS	SYMBOL	TYP	MAX	UNIT
	MBRS1045CT-Y	L 5A T 25°C	-	-	0.70	V
	MBRS1060CT-Y			-	0.80	V
	MBRS10100CT-Y	$I_F = 5A$, $T_J = 25$ °C		-	0.85	V
	MBRS10150CT-Y			-	0.88	V
	MBRS1045CT-Y			-	0.80	V
	MBRS1060CT-Y	1 10A T 0500		-	0.90	V
	MBRS10100CT-Y	$I_F = 10A, T_J = 25^{\circ}C$		-	0.95	V
Forward voltage per	MBRS10150CT-Y		\	-	0.98	V
diode ⁽¹⁾	MBRS1045CT-Y		V_{F}	-	0.57	V
	MBRS1060CT-Y	I _F = 5A, T _J = 125°C	- - - - -	-	0.65	V
	MBRS10100CT-Y			-	0.75	V
	MBRS10150CT-Y			-	0.78	V
	MBRS1045CT-Y	I _F = 10A, T _J = 125°C		-	0.67	V
	MBRS1060CT-Y			-	0.75	V
	MBRS10100CT-Y			-	0.85	V
	MBRS10150CT-Y			-	0.88	V
	MBRS1045CT-Y MBRS1060CT-Y MBRS10100CT-Y MBRS10150CT-Y	T _J = 25°C		-	100	μА
	MBRS1045CT-Y		I _R	-	15	mA
Reverse current @ rated V_{R} per diode ⁽²⁾	MBRS1060CT-Y	T _{.1} = 100°C		-	10	mA
	MBRS10100CT-Y MBRS10150CT-Y	-		-	-	mA
	MBRS1045CT-Y MBRS1060CT-Y	T, = 125°C		-	-	mA
	MBRS10100CT-Y MBRS10150CT-Y	1, 1200		-	5	mA

Notes:

- 1. Pulse test with PW = 0.3ms
- 2. Pulse test with PW = 30ms

ORDERING INFORMATION			
ORDERING CODE ⁽¹⁾	PACKAGE	PACKING	
MBRS10xCT-Y	TO-263AB (D ² PAK)	800 / Tape & Reel	

Notes:

1. "x" defines voltage from 45V(MBRS1045CT-Y) to 150V(MBRS10150CT-Y)

Fig.2 Typical Junction Capacitance



CHARACTERISTICS CURVES

 $(T_A = 25^{\circ}C \text{ unless otherwise noted})$

Fig.1 Forward Current Derating Curve

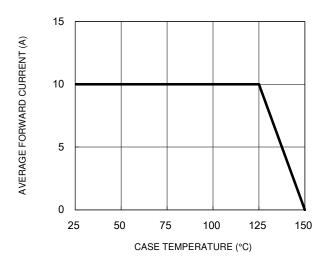


Fig.3 Typical Reverse Characteristics

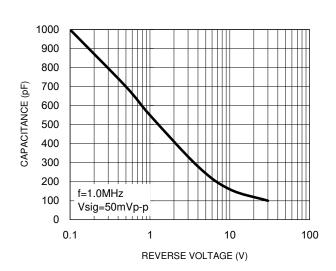
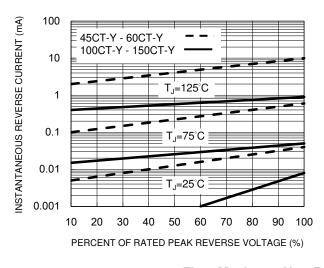


Fig.4 Typical Forward Characteristics



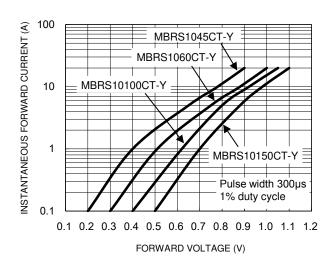
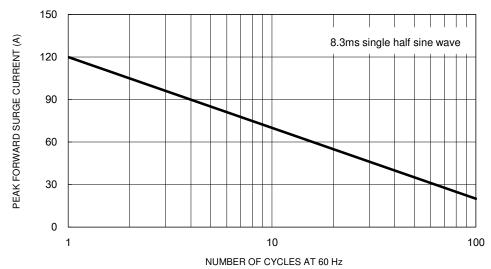


Fig.5 Maximum Non-Repetitive Forward Surge Current



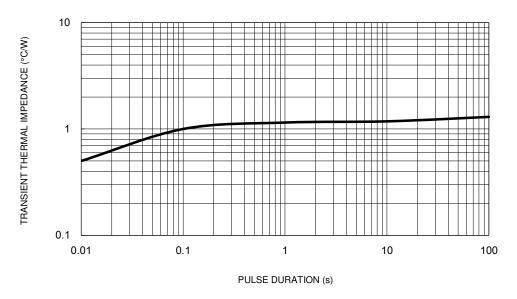
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CHARACTERISTICS CURVES

 $(T_A = 25^{\circ}C \text{ unless otherwise noted})$

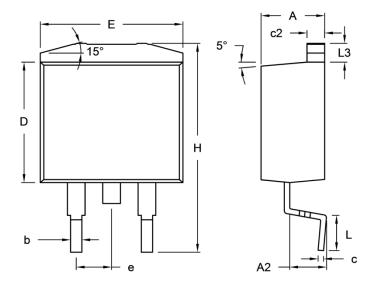
Fig.6 Typical Transient Thermal Impedance





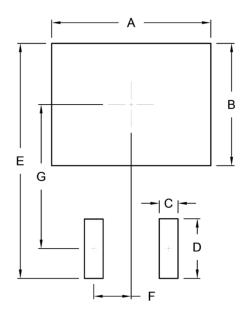
PACKAGE OUTLINE DIMENSIONS

TO-263AB (D²PAK)



DIM	Unit (mm)		Unit ((inch)	
DIM.	Min.	Max.	Min.	Max.	
Α	4.44	4.70	0.175	0.185	
A2	2.03	2.79	0.080	0.110	
b	0.68	0.94	0.027	0.037	
С	0.36	0.53	0.014	0.021	
c2	1.14	1.40	0.045	0.055	
D	8.25	9.25	0.325	0.364	
E	-	10.50	-	0.413	
е	2.41	2.67	0.095	0.105	
Н	14.60	15.88	0.575	0.625	
L	2.29	2.79	0.090	0.110	
L3	1.14	1.40	0.045	0.055	

SUGGESTED PAD LAYOUT



Symbol	Unit (mm)	Unit (inch)
Α	10.80	0.425
В	8.30	0.327
С	1.27	0.050
D	4.05	0.159
E	15.95	0.628
F	2.54	0.100
G	9.775	0.385

MARKING DIAGRAM



P/N = Marking Code G = Green Compound

YWW = Date Code = Factory Code



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